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LECTURE #14: RAM & ROM

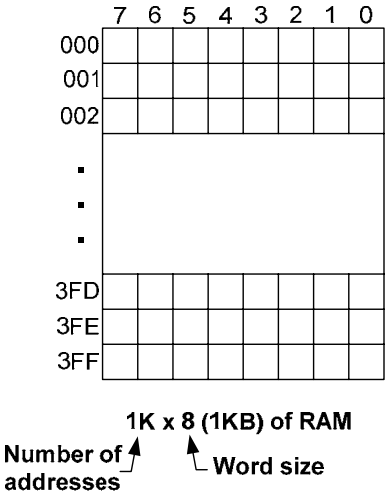
EEL 3701: Digital Logic and Computer Systems

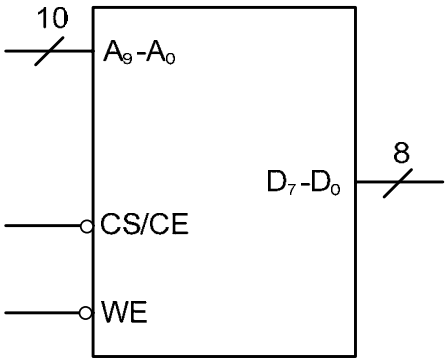
Based on lecture notes by Dr. Eric M. Schwartz

RAM = "Random Access Memory"

Static RAM (SRAM):

- SRAM is *volatile*, meaning that it only retains data while the power is on.
- Typical access times for CMOS based SRAM are around 10ns-100ns
  - Other types of SRAM types are available
- Memory can be viewed as a *vector of registers*
- Each register is indexed by an *address* (a number, usually in hexadecimal).



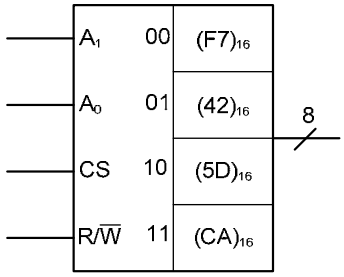


- Memory volume terminology:
  8 bits = 1 byte, 4 bits = 1 nibble,
  2^{10} = 1024 = "1K" (kilo-), 2^{20} = "1M" (mega-),
  2^{30} = "1G" (giga-), 2^{40} = "1T" (tera-)

- Memory requires n address lines, where 2^n is the number of memory addresses.
- Usually, the number of output lines is the same as the word size.
- Data lines are usually bi-directional (time-multiplexed)
  - Serve as an input when the "Write" state is True
  - Serve as an output when the "Read" state is True

Example: A 1KB RAM with an 8 bit word size (see figure above) requires:
10 address lines (A_9-A_0)
8 data lines (D_7-D_0)
Some control lines:
Chip Select (CS), Chip Enable (CE), Write Enable (WE),
Read (RD), Output Enable (OE), etc.

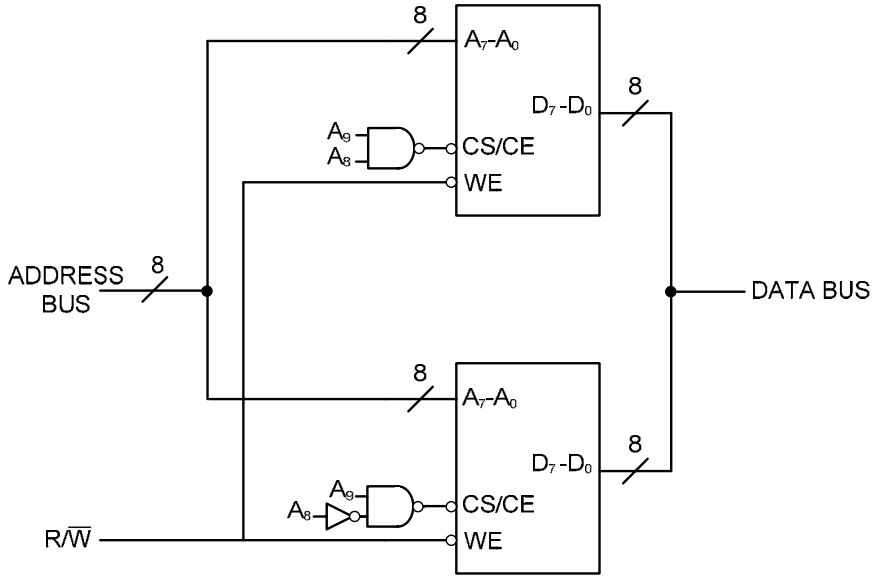
Example: A 4 x 8 (4-Byte) SRAM:



4 Bytes of RAM

(The following assumes that CS is True.)
- What output do we get if we "Read" $A_1 = 0$ and $A_0 = 1$? $(42)_{16}$
- How can we change $(CA)_{16}$ to $(F1)_{16}$?
  - Pull Read/Write low and introduce $(F1)_{16}$ on the data bus.

Example: Construct a 512 x 8 memory module from two 256 x 8 SRAM's.
The module should be wired to interface with a microprocessor that has 10 address lines, 8 data bits, and the necessary control bits.

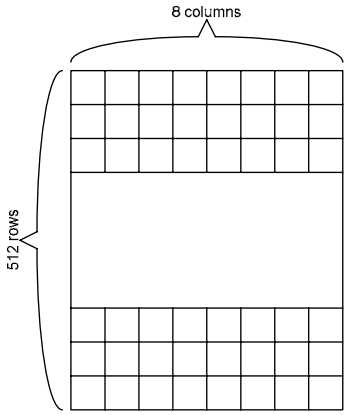


Address Wiring Diagram Combining Two 256-Byte Memories into a 512-Byte Memory

- Where in memory are these located?
  Answer: $300-$3FF and $200-$2FF

(Note: Symbols: $ => Hexadecimal, @ => Octal, % => Binary)
- How could we move them from "high" memory to "low" memory?
  - On the first, swap the NAND for an OR.
  - On the second, move the NOT gate from A_8 to A_9.
- Could you mix around the address lines?
  - Yes, but the data wouldn't be contiguous with normal addressing.

- Sometimes RAM is organized like a matrix internally:



4KB of RAM

- How many address lines would this RAM require?
  12, 3 for the columns and 9 for the rows.
- Does the internal arrangement matter to the user?
  No. The inputs and outputs works the same.

Dynamic RAM (DRAM):

- DRAM is also *volatile* RAM.
- Uses RAS and CAS (Row/Column Address Select)
  - Always uses a matrix architecture.
  - Row/Column addressing are time-multiplexed on the same address lines.

PRO:

1) Higher data density than SRAM (more data in less area = less cost)
   - 16MB (2^{24}) and even larger
2) Faster access time than SRAM

CON:

1) Must be periodically refreshed (re-written) or the data will be lost.

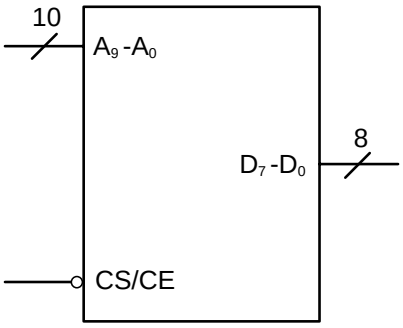
Read Only Memory (ROM):

- ROM is *non-volatile*, meaning that the data is saved even without power.
- ROM cannot be changed "on the fly."

Types of ROM:

ROM (masked ROM): Set by manufacturer. Cannot be modified.
PROM (Programmable ROM): You program once by blowing fuses.
EPROM (Erasable PROM): Reprogrammable. Erase using UV light.
EEPROM (Electrically EPROM): Erased with voltage pulses.
FLASH EEPROM: Newer and cheaper than standard EEPROM
-Example: USB Flash Drives

- ROM is used for storing unchanging software
  - i.e. Bootstraps for startup, BIOS (Basic I/O Services), etc.



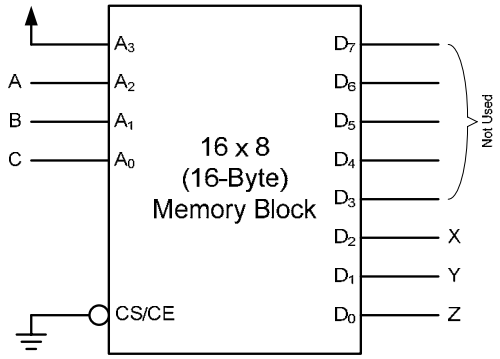
1K x 8 (1KB) of ROM

Note: There is no "Write Enable" input. Poorly written software may attempt to write to ROM. Without precautions, this would cause a data collision on the bus (outputs connected together). To prevent this problem, hardware should include the "Read" signal (or NOT "Write") as part of the criteria for enabling ROM.

Implementing a Truth Table with Memory:

TruthTable

A	B	C	X	Y	Z
0	0	0	1	1	0
0	0	1	0	1	1
0	1	0	0	1	0
0	1	1	1	0	1
1	0	0	0	0	1
1	0	1	0	0	0
1	1	0	1	1	1
1	1	1	1	0	0



- Inputs are connected to the address lines (i.e. A_2, A_1, and A_0).
  - These look up a byte in memory, whose values become the output.
- Extra address lines (i.e. A_3) can be tied high or low.
  - This effects which part of the memory is used, but not the operations.
- Internally, the Truth Table output values are stored.
  - The outputs are the LSb's of the byte at the corresponding address.
  - Ex. Address 1000 should contain xxxxx110 (see Truth Table above).